

### BC635/637/639

# **Switching and Amplifier Applications**• Complement to BC636/638/640



#### 1. Emitter 2. Collector 3. Base

## **NPN Epitaxial Silicon Transistor**

**Absolute Maximum Ratings** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CER</sub>	Collector-Emitter Voltage at R <sub>BF</sub> =1KΩ		
OLIK	: BC635	45	V
	: BC637	60	V
	: BC639	100	V
V <sub>CES</sub>	Collector-Emitter Voltage		
CEG	: BC635	45	V
	: BC637	60	V
	: BC639	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage		
	: BC635	45	V
	: BC637	60	V
	: BC639	80	V
$V_{EBO}$	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	1	А
I <sub>CP</sub>	Peak Collector Current	1.5	Α
	Base Current	100	mA
I <sub>B</sub> P <sub>C</sub>	Collector Dissipation	1	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-65 ~ 150	°C

PW=5ms, Duty Cycle=10%

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0				
	: BC635		45			V
	: BC736		60			V
	: BC639		80			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =30V, $I_E$ =0			0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ =5V, $I_C$ =0			0.1	μΑ
h <sub>FE1</sub>	DC Current Gain : All	V <sub>CE</sub> =2V, I <sub>C</sub> =5mA	25			
h <sub>FE2</sub>	: BC635	V <sub>CE</sub> =2V, I <sub>C</sub> =150mA	40		250	
	: BC637/BC639		40		160	
h <sub>FE3</sub>	: All	$V_{CE}$ =2V, $I_{C}$ =500mA	25			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA			0.5	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> =2V, I <sub>C</sub> =500mA			1	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA, f=50MHz		100		MHz

## **Typical Characteristics**

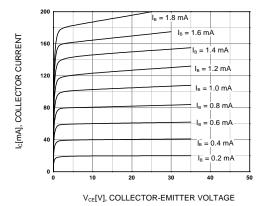


Figure 1. Static Characteristic

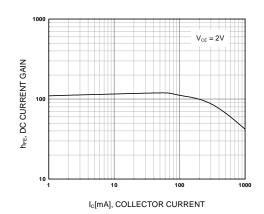


Figure 2. DC current Gain

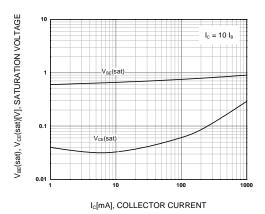


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

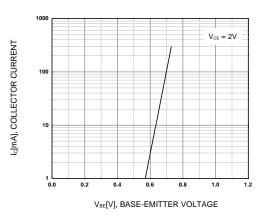


Figure 4. Base-Emitter On Voltage

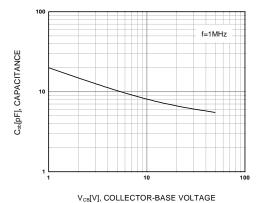
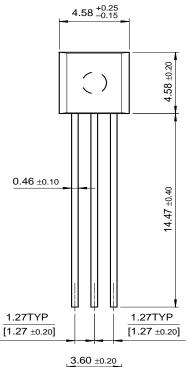
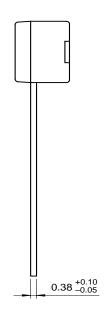


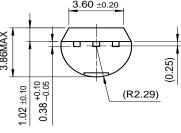
Figure 5. Collector Output Capacitance

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Dimensions in Millimeters

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